

Abstract of the Disclosure

A second cladding layer composed of p-AlGaN and a second contact layer composed of p-GaN are formed in this order on a light emitting layer composed of a nitride based semiconductor. A predetermined region of the second cladding layer and the second contact layer is removed, to form a ridge portion. A high-resistive current blocking layer, to which impurities have been added, is formed on an upper surface of a flat portion of the second cladding layer, which remains without being removed, and on both sidewalls of the ridge portion.